

3. The plasma processing method of Claim 1, further comprising:

adjusting, by the second device, the threshold value by using a moving average value calculated from series of the parameter,

wherein the series of the parameter include a parameter including at least one of the load impedance, the load resistance and the load reactance of the first high frequency power supply and the reflection wave coefficient of the first high frequency power in a state that impedance matching by the first matching device is completed in the completed second process among the second processes, or in each of the completed second process and a second process being performed.

4. The plasma processing method of Claim 1, further comprising:

controlling, by a power supply controller of the first high frequency power supply, the first high frequency power when a first moving average value and a second moving average value fall within a preset control range in each of the second processes, a frequency of the first high frequency power output in a first sub-period being adjusted such that the load impedance of the first high frequency power supply estimated from the first moving average value approximates to an output impedance of the first high frequency power supply, and the frequency of the first high frequency power output in a second sub-period being adjusted such that the load impedance of the first high frequency power supply estimated from the second moving average value approximates to the output impedance of the first high frequency power supply; and

controlling, by a power supply controller of the second high frequency power supply, the second high frequency power when a third moving average value and a fourth moving average value fall within a predetermined control range in each of the second processes, a frequency of the second high frequency power output in the first sub-period being adjusted such that a load impedance of the second high frequency power supply estimated from the third moving average value approximates to an output impedance of the second high frequency power supply, and the